L Number	Ditto	Search Text	DB	Time stamp
_ Number	Hits 8	118/719.ccls. and (chamber with pressure	USPAT;	2004/06/10 11:26
		with higher with prevent)	US-PGPUB	2004/00/10 11:20
	1	("20010040145").PN.	USPAT;	2003/02/26 10:13
10-1	_	,	US-PGPUB	,,,
_	196	156/345.24	USPAT;	2003/08/22 16:30
			US-PGPUB	
-	600	((156/345.24) or (156/345.51) or	USPAT;	2003/08/22 16:31
		(156/345.52) or (156/345.53)).CCLS.	US-PGPUB	
} <b>-</b>	177	(((156/345.24) or (156/345.51) or	USPAT;	2004/06/09 19:43
		(156/345.52) or (156/345.53)).CCLS.) and	US-PGPUB	1
		(control\$3 with (substrate wafer target)		
		with temperature)		
<b>-</b>	4	((((156/345.24) or (156/345.51) or	USPAT;	2003/08/22 17:14
		(156/345.52) or (156/345.53)).CCLS.) and	US-PGPUB	
		(control\$3 with (substrate wafer target)		
		with temperature)) and ((high with		
	728	densit\$3) same (low with ion\$6))	HODAM.	2004/06/09 19:44
-	128	(156/345.\$.CCLS.) and (control\$3 with	USPAT; US-PGPUB	2004/06/09 19:44
l _	142	(substrate wafer target) with temperature) (156/345.\$.CCLS.) and (control\$3 with	USPAT;	2004/06/09 19:44
-	142	(substrate wafer target) with temperature	US-PGPUB	2004/06/09 19:44
1		with etch\$3)	05-FGF0B	
ļ_	166	(156/345.\$.CCLS.) and (control\$4 with	USPAT;	2004/06/09 19:46
		(substrate wafer target) with temperature	US-PGPUB	
		with etch\$3)	33 10101	
_	131	(156/345.\$.CCLS.) and (control\$4 with	USPAT:	2004/06/09 19:46
		(substrate wafer target) with temperature	US-PGPUB	
		<pre>with during with (process\$3 treatm\$3))</pre>		
-	2	(156/345.\$.CCLS.) and (control\$4 with	USPAT;	2004/06/09 19:47
		(substrate wafer target) with temperature	US-PGPUB	
		with during with (process\$3 treatm\$3) with		
		damag\$3)		
-	39	(control\$4 with (substrate wafer target)	USPAT;	2004/06/09 19:56
		with temperature with during with	US-PGPUB	
	_	(process\$3 treatm\$3) with damag\$3)		
<del>-</del>	0	(118/719.ccls. 156/345.31.ccls.	USPAT;	2004/06/09 20:00
		156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	
ļ		204/298.35.ccls.) and (156/345.24.ccls.		
]		156/345.27.ccls. 204/298.03.ccls.		
		204/298.32.ccls.) and (control\$4 with		
ŀ		(substrate wafer workpiece) with temperature with during with (process\$3		
		treatm\$3) with damag\$3)		
l_	0	(118/719.ccls. 156/345.31.ccls.	USPAT;	2004/06/09 20:00
		156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	2004/00/09 20:00
		204/298.35.ccls.) and (156/345.24.ccls.	00 10105	
l		156/345.27.ccls. 204/298.03.ccls.		•
		204/298.32.ccls.) and (control\$4 with		
		(substrate wafer workpiece) with		
		temperature with damag\$3)		
-	79	• • • • • • • • • • • • • • • • • • • •	USPAT;	2004/06/09 20:00
		156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	
		204/298.35.ccls.) and (156/345.24.ccls.		
		156/345.27.ccls. 204/298.03.ccls.		
		204/298.32.ccls.)		
	24	,	USPAT;	2004/06/09 20:11
		156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	·
		204/298.35.ccls.) and (156/345.24.ccls.		
		156/345.27.ccls. 204/298.03.ccls.		
		204/298.32.ccls.) and (control\$4 with temperature )		
_	0	(118/719.ccls. 156/345.31.ccls.	USPAT;	2004/06/09 20:12
	9	156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	2004/00/03 20:12
ļ		204/298.35.ccls.) and (156/345.24.ccls.	30 10100	
		156/345.27.ccls. 204/298.03.ccls.		
		204/298.32.ccls.) and (control\$4 with		
		temperature with magnet\$ with propert\$3 )		
-	1	(118/719.ccls. 156/345.31.ccls.	USPAT;	2004/06/09 20:12
		156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	
		204/298.35.ccls.) and (control\$4 with		
		temperature with magnet\$ with propert\$3 )		

	1	/156/245 04 1 156/245 07	1	1
i -	] 3	(156/345.24.ccls. 156/345.27.ccls.	USPAT;	2004/06/09 20:13
		204/298.03.ccls. 204/298.32.ccls.) and	US-PGPUB	1
		(control\$4 with temperature with magnet\$		
•		with propert\$3 )		
7	133	(control\$4 with temperature with magnet\$	EPO; JPO;	2004/06/09 20:13
*		with propert\$3 )	DERWENT	
-	2	(control\$4 with temperature with magnet\$	EPO; JPO;	2004/06/09 20:14
		with propert\$3 with (during) with (treat\$4	DERWENT	
	1	process\$4))		
-	11	(control\$4 with temperature with magnet\$	USPAT:	2004/06/09 20:20
		with propert\$3 with (during) with (treat\$4	US-PGPUB	' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '
		process\$4))		
-	65	(control\$4 with temperature with magnet\$	USPAT;	2004/06/09 20:20
		with propert\$3 with (treat\$4 process\$4))	US-PGPUB	
-	65	(control\$4 with temperature with magnet\$	USPAT;	2004/06/09 20:21
		with propert\$3 with (treat\$4 process\$4))	US-PGPUB	2001,00,03 20.21
_	24	(control\$4 with temperature with magnet\$	EPO; JPO;	2004/06/09 20:21
		with propert\$3 with (treat\$4 process\$4))	DERWENT	2004/00/09 20.21
_	788	(156/345.\$.ccls. 118/715/733.\$.ccls.) and	USPAT;	2004/06/10 11:27
		((control\$4 with temperature) with	US-PGPUB	2004/00/10 11:2/
	1	(substrate wafer workpiece))	OB-FGFOB	:
_	177	(156/345.\$.ccls. 118/715/733.\$.ccls.) and	USPAT:	2004/06/10 11:27
	1	((control\$4 with temperature) with	US-PGPUB	2004/06/10 11:2/
		(substrate wafer workpiece) with (during))	03-16100	
_	13	(156/345.\$.ccls. 118/715/733.\$.ccls.) and	USPAT;	2004/06/10 13:13
	13	((control\$4 adj temperature) adj	US-PGPUB	2004/06/10 13:13
		(substrate wafer workpiece) adj (during))	US-PGPUB	
_	22	(156/345.\$.ccls.) and ((low adj	MADAM.	2004/26/12 12 14
	~~	temperature) adj (etch\$3))	USPAT;	2004/06/10 13:14
_	10	("5571366"   "5572366"   "5645683"	US-PGPUB	000.405400 10 10
	10		USPAT	2004/06/10 13:17
	i	"5695564"   "5695654"   "5700734"		
		"5756401"   "6008139"   "6046116"		
	,,	"6087264").PN.		
_	18	(156/345.\$.ccls. 216/\$.ccls.) and (plasma	USPAT;	2004/06/10 13:22
	]	same (low adj ion adj energy) same (high	US-PGPUB	
	l	adj density))		